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Nonlocal signatures of the chiral magnetic effect in the Dirac semimetal Bi$_{0.97}$Sb$_{0.03}$

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The field of topological materials science has recently been focusing on three-dimensional Dirac semimetals, which exhibit robust Dirac phases in the bulk. However, the absence of characteristic surface states in accidental Dirac semimetals (DSMs) makes it difficult to experimentally verify claims about the topological nature using commonly used surface-sensitive techniques. The chiral magnetic effect (CME), which originates from the Weyl nodes, causes an E · B-dependent chiral charge polarization, which manifests itself as negative magnetoresistance. We exploit the extended lifetime of the chirally polarized charge and study the CME through both local and nonlocal measurements in Hall bar structures fabricated from single crystalline flakes of the DSM Bi$_{0.97}$Sb$_{0.03}$. From the nonlocal measurement results we find a chiral charge relaxation time, which is over one order of magnitude larger than the Drude transport lifetime, underlining the topological nature of Bi$_{0.97}$Sb$_{0.03}$.

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I. INTRODUCTION

The electronic structure of bismuth-antimony alloys has been thoroughly studied in the 1960s and 70s and later regained attention when Bi$_{1-x}$Sb$_x$ was one of the first topological materials to be discovered [1]. It was proposed that at the topological transition point, which is at $x \sim 0.03$, an accidental band touching in the bulk of Bi$_{1-x}$Sb$_x$ makes this material a Dirac semimetal (DSM) [2–4]. A popular method to measure the topological nature of DSMs is through the detection of the chiral magnetic effect (CME) in electronic transport measurements. However, these signals are often obscured by the presence of parallel, nontopological conduction channels and are, more importantly, difficult to distinguish from other effects that may cause negative magnetoresistance, such as current jetting [5]. Parameswaran et al. [6] proposed to measure the CME nonlocally, using the extended lifetime of chirally polarized charge. For the Dirac semimetal Cd$_3$As$_2$, where two sets of Dirac cones with opposite chirality are separated in momentum space and protected by inversion symmetry, this measurement technique has been successfully used to measure the CME [7]. In this work, we present evidence for the presence of the chiral magnetic effect in the accidental Dirac semimetal Bi$_{0.97}$Sb$_{0.03}$, based on local and nonlocal magnetotransport results on crystalline, exfoliated flakes.

In a general Dirac semimetal, two Weyl cones of opposite chirality (often labeled as isospin degree of freedom [6]) are superposed in momentum space as depicted in Fig. 1(a). Their chiralities are defined through an integral of the Berry connection, $A_{k\pm} = i\langle \psi_{\pm} | \nabla_k | \psi_{\pm} \rangle$, over the Fermi surface (FS):

$$\chi_{\pm} = \frac{1}{2\pi} \oint_{FS} (\nabla_k \times A_{k\pm}) \cdot dS_k,$$

where $k$ is the wave vector. Using a basic representation of the Weyl nodes, $\psi_{\pm} = [e^{-i\phi} \sin(\phi/2), -\cos(\phi/2)]^T$ (where $\theta$ is the in-plane angle in momentum space, with $\theta = 0$ along the $k_z$ axis, and $\phi$ is the polar angle with respect to $k_z$), one finds $\chi_{\pm} = \pm 1$. These nodes with opposite chiralities always come in pairs and, when the degeneracy of the Weyl cones is lifted, they are connected in momentum space by a surface state known as a Fermi arc. In mirror symmetry-protected Dirac systems, such as Cd$_3$As$_2$, different pairs of Weyl nodes can also be connected by Fermi arcs, which has been experimentally observed [8]. Bi$_{0.97}$Sb$_{0.03}$ contains accidental Dirac points at the three $L$ points [2]. The crossings at these Dirac points are not protected by any symmetry, and should not be connected by Fermi arcs. However, upon breaking time-reversal symmetry with an external magnetic field, the Dirac cones split into two Weyl cones of opposite chirality, in which case Bi$_{0.97}$Sb$_{0.03}$ behaves very similar to Cd$_3$As$_2$.

A more in-depth discussion on the topological properties of Bi$_{0.97}$Sb$_{0.03}$ compared to those of Cd$_3$As$_2$ can be found in Sec. A of the Supplemental Material [9].

The different chiral nodes correspond to a source and drain of Berry curvature ($\Omega_{k\pm} = V_k \times A_{k\pm}$), which in turn behaves as a magnetic field in momentum space. Taking this momentum space analog of the magnetic field into account in the equations of motion, one ends up with an expression for chiral charge pumping $\partial \rho_{\pm} / \partial t$ in external parallel electric and magnetic fields [10,11]:

$$\frac{\partial \rho_{\pm}}{\partial t} = f(\Omega_k) \frac{e^3}{4\pi^2 \hbar^2} E \cdot B,$$

where $E$ and $B$ are the electric and magnetic fields respectively, and $f(\Omega_k)$ represents the chirality dependence. The result from this semiclassical argument can also been obtained in the quantum limit [12]. This chiral charge pumping creates a difference in chemical potential in the two Weyl cones, causing a net imbalance in chirality, which eventually relaxes by means of impurity scattering. However, the orthogonality of the two degenerate Weyl cones with different isospin and the large momentum difference between different valleys...
scattering events is the likely dominant chiral relaxation process in Bi_{0.97}Sb_{0.03}.

II. METHODS AND CHARACTERIZATION

To characterize the Bi_{0.97}Sb_{0.03} crystals (which are grown as described by Li et al. [3]), several devices with contacts in a Hall bar configuration were fabricated. For all devices in this work, flakes of Bi_{0.97}Sb_{0.03} were exfoliated from single crystals onto SiO_{2}/Si++ substrates. Contact leads were defined using standard e-beam lithography, followed by sputter deposition of 120 nm Nb with a few nm of Pd as capping layer, and lift-off. Then, the flakes themselves were structured using another e-beam lithography step, now followed by Ar⁺ milling. Magnetotransport measurements were conducted at 10 K in He-4 cryostats.

The inset of Fig. 2(a) shows a schematic overview of the measurement setup as used for local magnetotransport measurements. A current is sourced through the outer contacts and voltages are measured at the contacts in between. As observed earlier by Kim et al. [2], the magnetoresistance of Bi_{0.97}Sb_{0.03}, shown in Fig. 2(a), exhibits negative magnetoresistance for parallel electric and magnetic fields. This negative magnetoresistance is considered to be an indication of the CME [2,13–15]. While the CME in Bi_{0.97}Sb_{0.03} originates from the bulk electrons, the magnetoresistance data shows no Shubnikov-de Haas (SdH) oscillations corresponding to the bulk electron pockets, despite the low effective mass and high mobility of these electrons [16]. We will comment on this later. However, in accordance with previous measurements on flakes of Bi_{0.97}Sb_{0.03}, we do observe SdH oscillations originating from the bulk hole pocket in different samples made of the same single crystal (see Sec. B of the Supplemental Material [9]).

Figure 2(b) shows the results of a Hall-type measurement. By tensor inversion of the measured longitudinal and Hall resistances, the longitudinal and transverse conductances were obtained. In Fig. 2(c), the conductances are fitted using a multiband model, which takes two surface and two bulk conduction channels into account [3]. For the bulk electrons, we obtain a bulk electron density of \( n_B^e = 3.0 \times 10^{22} \text{ m}^{-3} \), where
we have used a flake thickness of 200 nm. For anisotropic Fermi velocities of $v_1 = 0.8 \times 10^5$ m/s and $v_2 = 10 \times 10^5$ m/s [1], this would indicate that the Fermi energy lies only $E_F = \hbar (\pi^2 n_0 v_1 v_2 / 3)^{1/3} = 13$ meV above the Dirac point. The bulk charge carrier mobilities as obtained from the multiband fit are lower than those found in unstructured devices [3]. This is in line with the absence of SdH oscillations in this measurement, which can be attributed to the device dimensions being of the same order as the cyclotron radius, and to disorder due to etching at the device edges. The consequent broadening of the Landau levels does not hamper the presence of the CME [7]. For a conservative effective mass of $m_{e,h} = 0.05 m_0$ [3], the bulk electron and hole mobilities of $\mu = 0.65$ m$^2$/Vs give us an estimate of the momentum relaxation time: $\tau_c = \mu m/e \approx 1.8 \times 10^{-13}$ s. This is in line with the absence of SdH oscillations in this measurement, which can be attributed to the device dimensions being of the same order as the cyclotron radius.

The nonlocal measurement setup is designed such that we can measure the coupling between the polarization of chirality and an external magnetic field at different distances from the polarization source, and is shown in Fig. 3. A current is sourced from contact 8 to 1, as indicated by the blue arrow. By applying a magnetic field parallel to the current, a chiral charge imbalance is induced. As the charge diffuses away from the polarizing source, the polarization becomes weaker and so does the measurable voltage of the polarized charge in the external magnetic field. We measure the voltages locally ($V_{L} \equiv V_{01} = V_{8} - V_{1}$) and nonlocally ($V_{1} \equiv V_{72}$, $V_{2} \equiv V_{63}$ and $V_{3} \equiv V_{54}$). To be able to distinguish the Ohmic (i.e., normal diffusion) and CME signals, the voltage terminals are located at distances similar to both the expected Ohmic and chiral relaxation lengths.

When studying the CME, in the ideal case one measures the nonlocal response of the chiral anomaly as a function of the applied magnetic field only, i.e., keeping the applied electric field at the source contacts constant. However, due to the low resistance of these samples, we cannot voltage bias our sample and must resort to a current source, thereby causing the current to be constant as a function of the applied magnetic field. When measuring the local electric field, we find that this field is dependent on the magnetic field as well.

In order to obtain a data set with a constant electric field at the source contacts, measurements were performed by sweeping the source current from $0$–$10 \mu A$ for every magnetic field point, resulting in local and nonlocal magnetoresistance curves for a range of source currents $V_{L1,2,3}(I, B)$. An example of such a set of magnetoresistance curves for a fixed source current is shown in Fig. 4(a). The local voltage, $V_{L1}(I, B)$, is shown in the inset and should be kept constant, which is achieved by varying the source current $I(V_{L1} = \text{cst.}, B)$. In Fig. 4(b), we present the resulting voltages $V_{NL}(I, B)$, when the local electric field is kept constant in this way. Note that the local voltage, shown in the inset of Fig. 4(b), is now constant. Using this method, the magnetic field dependence of the nonlocal signals can be studied without side effects from the local magnetoresistance. For more information on this procedure, see Sec. C of the Supplemental Material [9].

### III. RESULTS

The measured local voltage $V_{L1}$, presented in the inset of Fig. 4(a), is in good agreement with the expected resistance based on the four-point resistance, taking the size of the channels into account. This indicates that the effects of contact resistances are negligible. Figure 4(b) shows the nonlocal voltages measured at different distances as a function of the applied magnetic field. Here, the electric field at the source...
FIG. 5. Diffusion lengths. Top: Atomic force microscopy image of a Bi\textsubscript{0.97}Sb\textsubscript{0.03} single-crystal flake, structured into a device for nonlocal measurements and contacted with Nb leads. Bottom: Normalized strength of the Ohmic (zero field) and CME (from fit) contributions to the signals measured at the voltage probes. The CME strength persists over longer distances than the Ohmic signal.

side is kept constant. At zero magnetic field, the measured voltages drop with increasing distance from the source. Furthermore, at all distances we observe a decreasing voltage with increasing magnetic field, which we attribute to the CME. The CME is not dominant for the entire magnetic field range as both at low and high fields, the voltage increases slightly with magnetic field. Kim et al. attribute the low field MR to weak antilocalization [2]. High field deviations from the CME signal may originate from higher-order terms, which are not taken into account in this work.

We have identified three possible causes of the small asymmetry of the data. First and foremost is the device asymmetry with respect to the source channel, but variations in sample thickness and imperfections in the structuring process may also be contributing factors. Figure 4(c) shows the symmetrized nonlocal voltages. We fitted the intermediate field data between 2 T and 5.5 T with a model that subtracts the constant Ohmic contribution, and extracts the diffusion of the chiral charge as given by Parameswaran et al. [6]:

\[ V_{NL}(x) = -\left(\frac{B}{\gamma + B}\right)^2 e^{-|x|/L_{CME}} + V_{Ohmic}, \]

Here \( x \) is the distance between the source and the nonlocal probes, \( \gamma \) is proportional to the conductance at the metal contact and \( L_{CME} \) is the diffusion length of the chiral charge polarization. The fit agrees well with the data for intermediate magnetic fields and it gives a diffusion length of \( 1.07 \mu m \). Using \( L_{CME} = \sqrt{D \tau_{CME}} \) and \( D = (1/3) v_F \mu m \), with \( I_m = v_F \tau_{CME} \), we find a chiral polarization lifetime of \( \tau_{CME} \approx 3.7 \times 10^{-12} s \), which is over one order of magnitude longer than the Drude transport lifetime \( \tau_c \approx 1.4 \times 10^{-13} s \).

The dependence of the normalized Ohmic and CME contributions to the measured voltages is presented in Fig. 5, along with an atomic force microscopy (AFM) image of the device. Here, the amplitudes of the best fits are used to represent the CME strength. The measured Ohmic (zero-field) contribution at all voltage terminals is shown for comparison. The Ohmic contribution of the device is also modeled numerically, where the shown solid curve is a line cut along the horizontal part of the device (see Sec. D of the Supplemental Material [9]). The simulated Ohmic contributions fit very well to the measured data, emphasizing the good homogeneity of the flake. The most notable feature of Fig. 5 is that the chiral polarization of the charge carriers has a significantly longer relaxation length than the Drude transport lifetime.

To study the temperature dependence of the CME in Bi\textsubscript{0.97}Sb\textsubscript{0.03}, another device was measured at higher temperatures. This device has larger channel widths and spacing as can be seen in the AFM image of the device in Fig. 6(a). Figure 6(b) shows the measured voltages at the nonlocal contacts closest to the source, which present the most striking features. It is apparent that for all temperatures displayed in this figure, the magnetoresistance is strongly negative and that this nonlocal voltage decreases as temperature increases. Through the same fitting procedure described above, the chiral charge polarization diffusion length is extracted for each temperature and shown in Fig. 6(c) (more information on this procedure can be found in Sec. F of the Supplemental Material [9]). In contrast to what has been found for Cd\textsubscript{3}As\textsubscript{2}...
[7], the chiral diffusion length in Bi$_{0.97}$Sb$_{0.03}$ does not seem to be constant with increasing temperature, but rather decreases linearly. The increasing relaxation rate $\tau_{\text{CME}}^{-1}$ with increasing temperature, indicates that inelastic processes are responsible for the relaxation of the chiral polarization in Bi$_{0.97}$Sb$_{0.03}$.

IV. CONCLUSIONS

In summary, we studied the chiral magnetic effect in Bi$_{0.97}$Sb$_{0.03}$ through transport measurements in local and non-local configurations. First, we characterized the exfoliated crystalline Bi$_{0.97}$Sb$_{0.03}$ flakes using a Hall-type measurement. Here, we identified contributions from two bulk bands, one of them corresponding to the electron pockets with a linear dispersion and a Fermi level close to the Dirac point. When subjected to parallel electric and magnetic fields, local measurements on our Bi$_{0.97}$Sb$_{0.03}$ devices show a pronounced negative magnetoresistance, an indication of the chiral magnetic effect.

In a nonlocal configuration, we measured voltages that strongly decrease with increasing magnetic field, which we attribute to the chiral magnetic effect. As voltage contacts are located farther away from the polarization source, the measured chiral magnetic effect weakens. This weakening occurs at a much lower rate than the decay of the Ohmic signal, which is a consequence of the long lifetime of the chiral polarization $\tau_{\text{CME}}$. Furthermore, measurements at different temperatures show that the chiral charge diffusion length decreases with increasing temperature, emphasizing the role of inelastic scattering in the chiral charge relaxation process in Bi$_{0.97}$Sb$_{0.03}$. Both local and nonlocal measurements provide strong evidence of the presence of the chiral magnetic effect in the three-dimensional Dirac semimetal Bi$_{0.97}$Sb$_{0.03}$.

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